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Application Number	10/788,991
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First Named Inventor	Paul A. Farrar
Group Art Unit	2812
Examiner Name	L. Gurley
Attorney Docket Number	2269-5570 IUS (02-1122 01/IUS)

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		ANDRICACOS, Panos C., "Copper On-Chip Interconnections", The Electrochemical Society Interface, Spring 1999, pp. 32-37, Vol. 8, No. 1.	
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